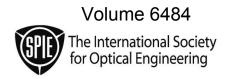
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Vertical-Cavity Surface-Emitting Lasers XI

Kent D. Choquette James K. Guenter Chairs/Editors

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Introduction

On January 24 and 25, 2007, the 11th Vertical Cavity Surface Emitting Lasers Conference was held as part of the SPIE Photonics West Symposium in San Jose, California. This proceedings volume contains the papers and reports written by the conference presenters who discussed their activities in 2006. The topics discussed included the continued development of commercial VCSEL products, new applications for VCSELs, and the renewed efforts to integrate VCSELs with other devices for new functionality.

Commercial VCSEL manufacture continues, where the milestone of greater than 100 million VCSELs deployed in the field was achieved in 2006. VCSELs for 10 Gb/s operation were discussed, with an emphasis on device reliability. Although data comm remains the dominant VCSEL application, other uses such as laser computer mice, atomic clocks, and high-power lasers for automotive or industrial sensing were proposed.

The papers presented at the 2007 VCSEL XI Conference included in these proceedings illustrate the present status of the continuing advancement of VCSEL optoelectronic technology.

Kent D. Choquette Jim Guenter